

### **IN THE CLAIMS**

Please amend the claims as follows.

1. (Amended) A method comprising:

forming a first dielectric layer above a first structure layer;

forming a first opening in the first dielectric layer;

forming a first copper layer above the first dielectric layer and in the first opening; and

measuring an actual thickness of the copper layer, measuring the actual thickness comprises averaging a plurality of thicknesses from a plurality of locations on said first copper layer;

comparing the actual thickness to a desired thickness; and

varying at least one parameter used to form the first copper layer in response to the actual thickness differing from the desired thickness.

22. (Amended) A system, comprising:

means for forming a first dielectric layer above a first structure layer;

means for forming a first opening in the first dielectric layer;

means for forming a first copper layer above the first dielectric layer and in the first opening;

means for measuring an actual thickness of the copper layer, measuring the actual thickness comprises averaging a plurality of thicknesses from a plurality of locations on said first copper layer;

means for comparing the actual thickness to a desired thickness; and

means for varying at least one parameter used to form the first copper layer in response to the actual thickness differing from the desired thickness.